

FIG. 1. a) Lifetime  $\tau$  at an excess carrier density of  $10^{15} \text{ cm}^{-3}$  as a function of line speed. Efficient passivation on planar substrates was obtained at all line speeds. b) Lifetime at an excess carrier density of  $10^{15} \text{ cm}^{-3}$  presented as a function of post-annealing conditions.

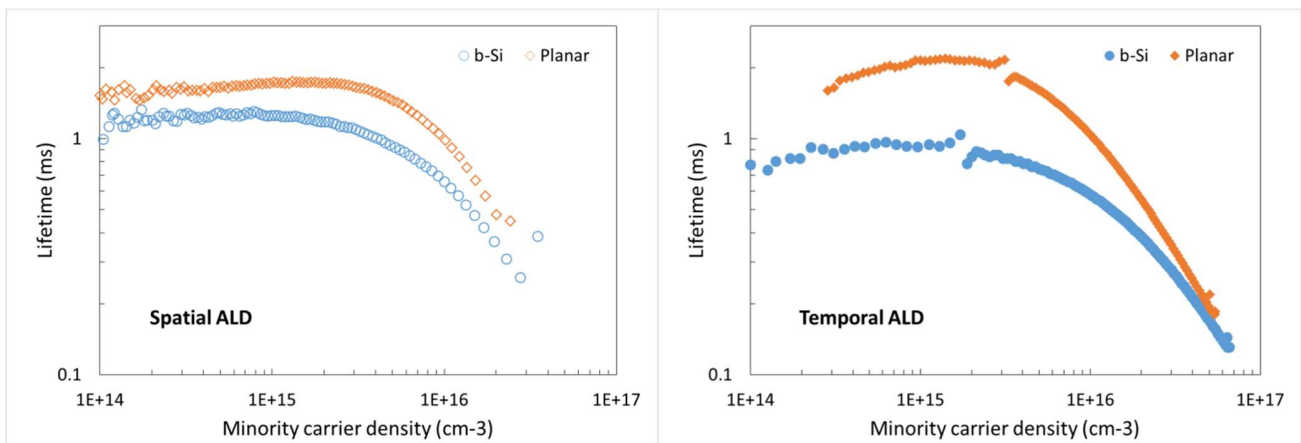


FIG. 2. Lifetime  $\tau$  of planar and b-Si samples coated with SALD and temporal ALD. SALD coated samples were annealed at 370°C in a H<sub>2</sub>/N<sub>2</sub> atmosphere, while temporal ALD samples were annealed at 425°C in a N<sub>2</sub> atmosphere.

## References

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